MUSES

High Quality Audio , J-FET Input, Dual Operational Amplifier

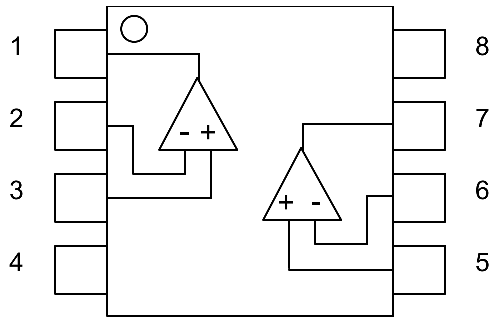
The **MUSES01** is a dual J-FET input high quality audio operational amplifier, which is optimized for high-end audio and professional audio applications with advanced circuitry and layout, unique material and assembled technology by skilled-craftwork.

It is the best for audio preamplifiers, active filters, and line amplifiers with excellent sound.

■ FEATURES

●Operating Voltage	Vopr=±9V to ±16V
●Output noise	9.5nV/√Hz at f=1kHz
●Input Offset Voltage	0.8mV typ. 5mV max.
●Input Bias Current	200pA typ. 800pA max. at Ta=25°C
●Voltage Gain	105dB typ.
●Slew Rate	12V/µs typ.
●Bipolar Technology	
●Package Outline	DIP8

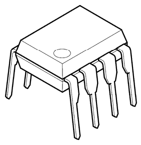
■ PIN CONFIGURATION



PIN FUNCTION

1. A OUTPUT
2. A -INPUT
3. A +INPUT
4. V-
5. B +INPUT
6. B -INPUT
7. B OUTPUT
8.V+

■ PACKAGE OUTLINE



MUSES01

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V^+/V^-	±18	V
Common Mode Input Voltage	V_{ICM}	±15 (Note1)	V
Differential Input Voltage	V_{ID}	±30	V
Power Dissipation	P_D	910	mW
Output Current	I_O	±25	mA
Operating Temperature Range	T_{opr}	-40 to +85	°C
Storage Temperature Range	T_{stg}	-50 to +150	°C

(Note1) For supply Voltages less than ±15 V, the maximum input voltage is equal to the Supply Voltage.

■ RECOMMENDED OPERATING CONDITION (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V^+/V^-	-	±9	-	±16	V

■ ELECTRIC CHARACTERISTICS

DC CHARACTERISTICS (V^+/V^-=±15V, Ta=25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Operating Current	I_{cc}	No Signal, R_L=∞	-	8.5	12.0	mA
Input Offset Voltage	V_{IO}	Rs≤10kΩ (Note2)	-	0.8	5.0	mV
Input Bias Current	I_B	(Note2, 3)	-	200	800	pA
Input Offset Current	I_{IO}	(Note2, 3)	-	100	400	pA
Voltage Gain	A_V	R_L≥2kΩ, V_o=±10V	90	105	-	dB
Common Mode Rejection Ratio	CMR	V_{ICM}=±8V (Note4)	60	75	-	dB
Supply Voltage Rejection Ratio	SVR	V^+/V^-=±9.0 to ±16.0V (Note2, 5)	70	83	-	dB
Max Output Voltage 1	V_{OM1}	R_L=10kΩ	±12	±13.5	-	V
Max Output Voltage 2	V_{OM2}	R_L=2kΩ	±10	±12.5	-	V
Input Common Mode Voltage Range	V_{ICM}	CMR≥60dB	±8	±9.5	-	V

(Note2) Measured at VICM=0V

(Note3) Written by the absolute rate.

(Note4) CMR is calculated by specified change in offset voltage. (VICM=0V to +8V and VICM=0V to −8V)

(Note5) SVR is calculated by specified change in offset voltage. (V+/V−=±9V to ±16V)

AC CHARACTERISTICS (V^+/V^-=±15V, Ta=25°C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gain Bandwidth Product	GB	f=10kHz	-	3.3	-	MHz
Unity Gain Frequency	f_T	A_V=+100, R_S=100Ω, R_L=2kΩ, C_L=10pF	-	3.0	-	MHz
Phase Margin	ϕ_M	A_V=+100, R_S=100Ω, R_L=2kΩ,C_L=10pF	-	60	-	deg
Input Noise Voltage1	V_{NI}	f=1kHz, A_V=+100, R_S=100Ω	-	9.5	-	nV/√Hz
Input Noise Voltage2	V_{N2}	RIAA, R_S =2.2kΩ, 30kHz LPF	-	1.2	3.0	µVrms
Total Harmonic Distortion	THD	f=1kHz, A_V=+10, R_L=2kΩ, Vo=5Vrms	-	0.002	-	%
Channel Separation	CS	f=1kHz, A_V=-+100, R_S=1kΩ, R_L=2kΩ	-	150	-	dB
Positive Slew Rate	+SR	A_V=1, V_{IN}=2V_{p-p}, R_L=2kΩ, C_L=10pF	-	12	-	V/µs
Negative Slew Rate	-SR	A_V=1, V_{IN}=2V_{p-p}, R_L=2kΩ, C_L=10pF	-	13	-	V/µs

■ Application Notes

•Package Power, Power Dissipation and Output Power

IC is heated by own operation and possibly gets damage when the junction power exceeds the acceptable value called Power Dissipation P_D. The dependence of the MUSES01 P_D on ambient temperature is shown in Fig 1. The plots are depended on following two points. The first is P_D on ambient temperature 25°C, which is the maximum power dissipation. The second is 0W, which means that the IC cannot radiate any more. Conforming the maximum junction temperature Tjmax to the storage temperature Tstg derives this point. Fig.1 is drawn by connecting those points and conforming the P_D lower than 25°C to it on 25°C. The P_D is shown following formula as a function of the ambient temperature between those points.

$$\text{Dissipation Power} \quad P_D = \frac{\text{Tjmax - Ta}}{\theta\text{ja}} \quad \text{[W] (Ta=25°C to Ta=150°C)}$$

Where, θja is heat thermal resistance which depends on parameters such as package material, frame material and so on. Therefore, P_D is different in each package.

While, the actual measurement of dissipation power on MUSES01 is obtained using following equation.

(Actual Dissipation Power) = (Supply Voltage V_{DD}) X (Supply Current I_{DD}) – (Output Power Po)

The MUSES01 should be operated in lower than P_D of the actual dissipation power.

To sustain the steady state operation, take account of the Dissipation Power and thermal design.

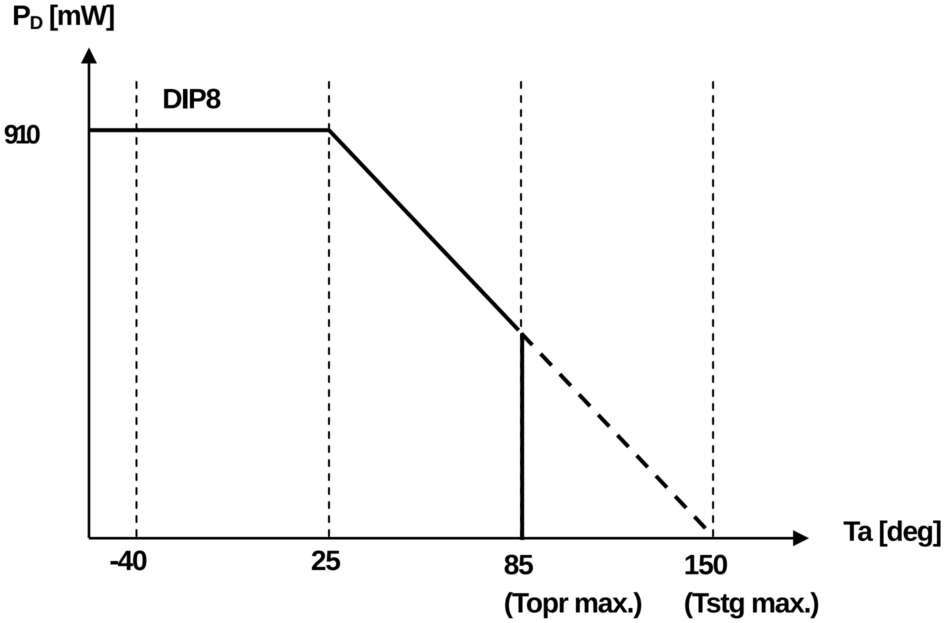
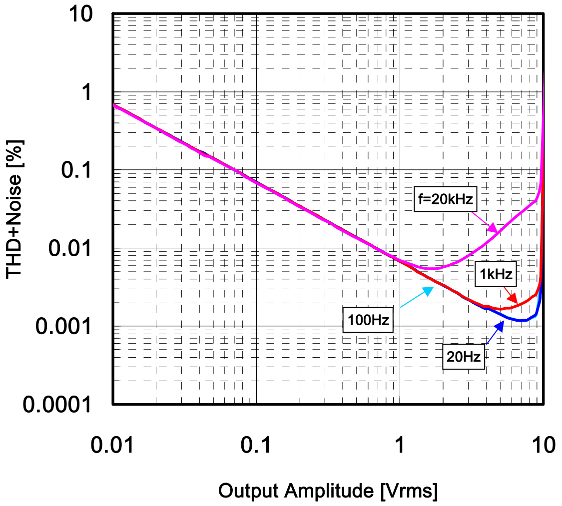


Fig.1 Power Dissipations vs. Ambient Temperature on the MUSES01

■ TYPICAL CHARACTERISTICS

TOTAL HARMONIC DISTORTION + NOISE
vs OUTPUT AMPLITUDE (FREQUENCY)

$V^+/V^-=\pm16V, A_V=+10$, Rg=1kohm,Rf=9.1kohm, R_L=2kohm,Ta=25℃



TOTAL HARMONIC DISTORTION + NOISE
vs OUTPUT AMPLITUDE (FREQUENCY)

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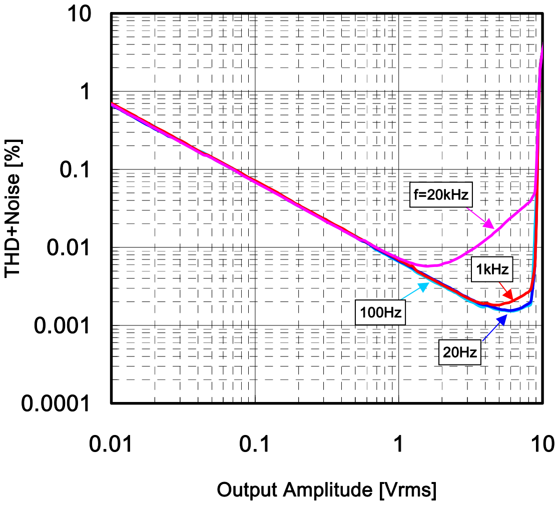
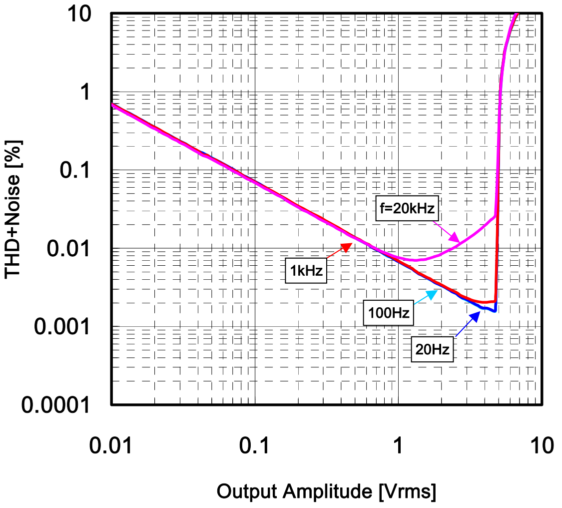


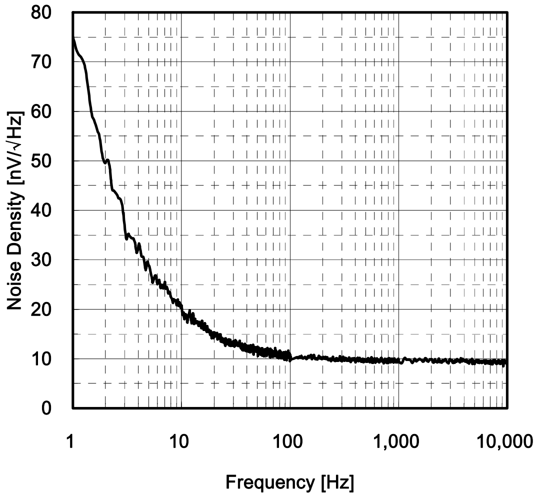
TOTAL HARMONIC DISTORTION + NOISE
vs OUTPUT AMPLITUDE (FREQUENCY)

$V^+/V^-=\pm9V, A_V=+10$, Rg=1kohm,Rf=9.1kohm, R_L=2kohm,Ta=25℃



EQUIVALENT INPUT NOISE DENSITY vs
FREQUENCY

$V^+/V^-=\pm16V, A_V=+100$, Rs=100ohm, $R_L=\infty$, Ta=25℃



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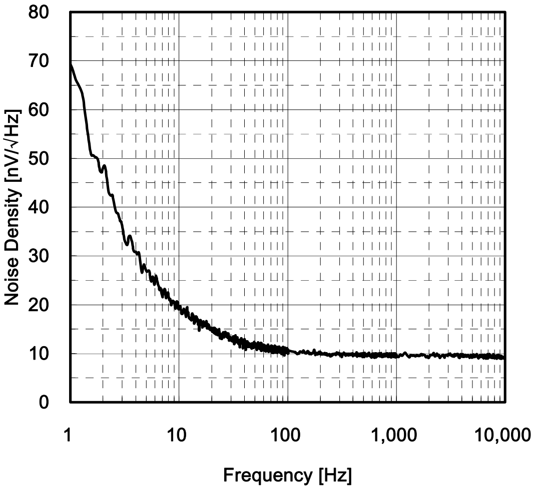

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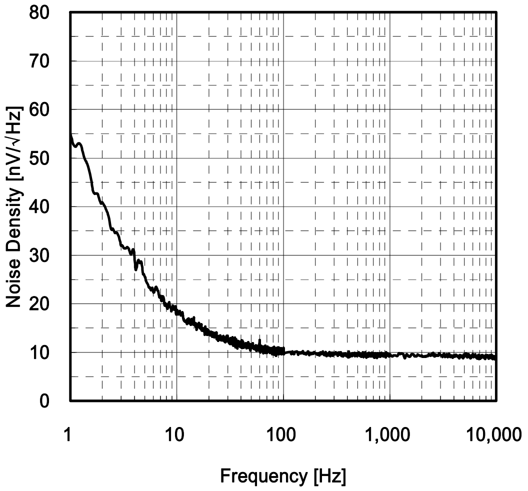
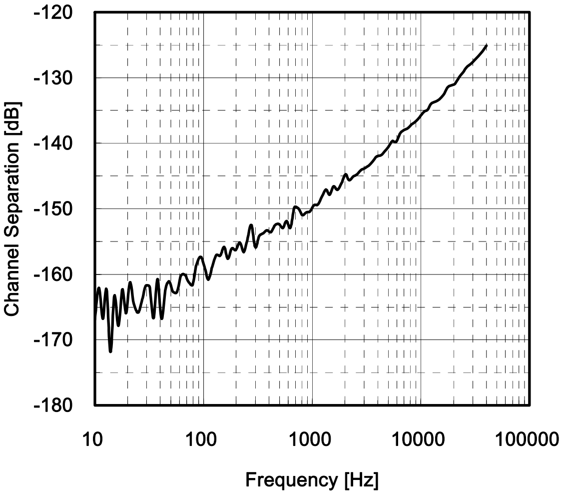


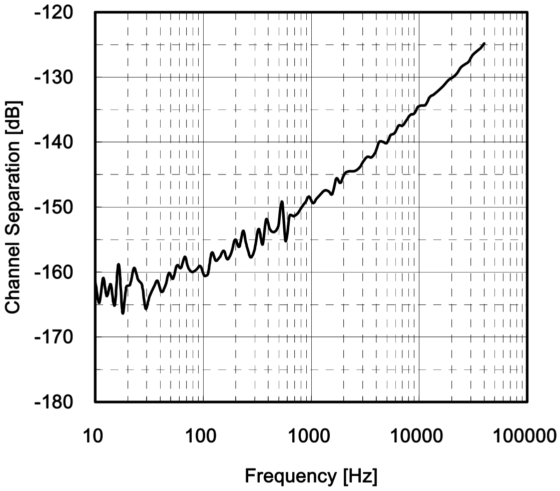
CHANNEL SEPARATION vs FREQUENCY

V^+/V^-=±16V,A_V=-100, R_S=1kohm, R_L=2kohm, Vo=5Vrms, Ta=25℃



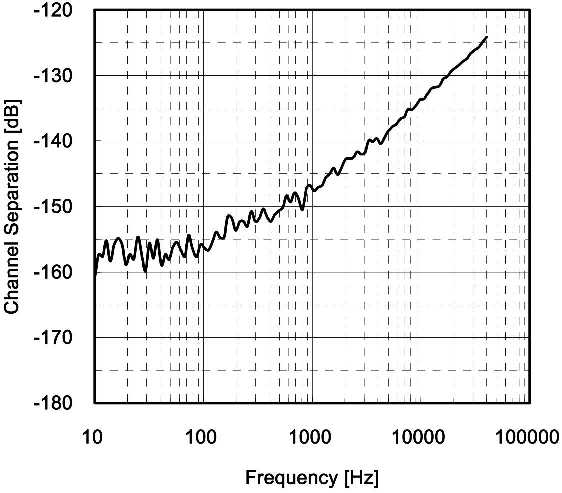
CHANNEL SEPARATION vs FREQUENCY

V^+/V^-=±15V,A_V=-100, R_S=1kohm, R_L=2kohm, Vo=5Vrms, Ta=25℃



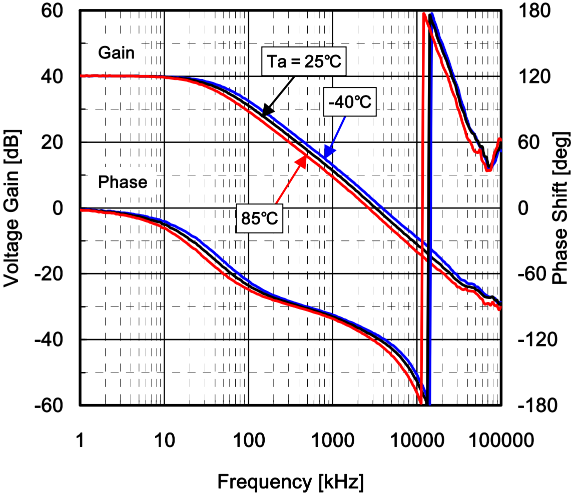
CHANNEL SEPARATION vs FREQUENCY

V^+/V^-=±9V,A_V=-100, R_S=1kohm, R_L=2kohm, Vo=4Vrms, Ta=25℃



CLOSED-LOOP GAIN/PHASE vs FREQUENCY (TEMPERATURE)

V^+/V^-=±16V, A_V=+100, R_S=100ohm, R_T=50ohm,R_L=2kohm,C_L=10pF
V_{IN}=-30dBm,Vicm=0V



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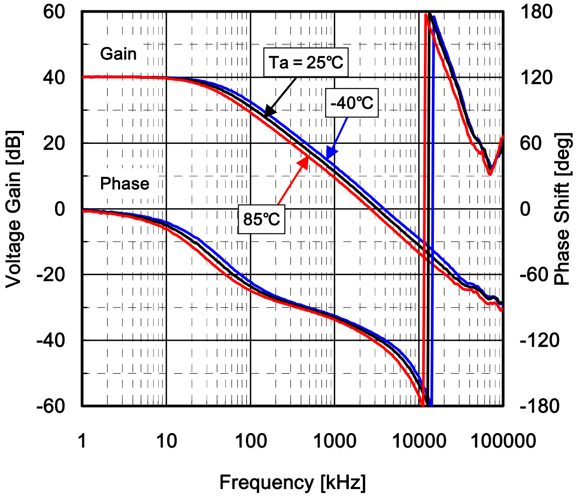

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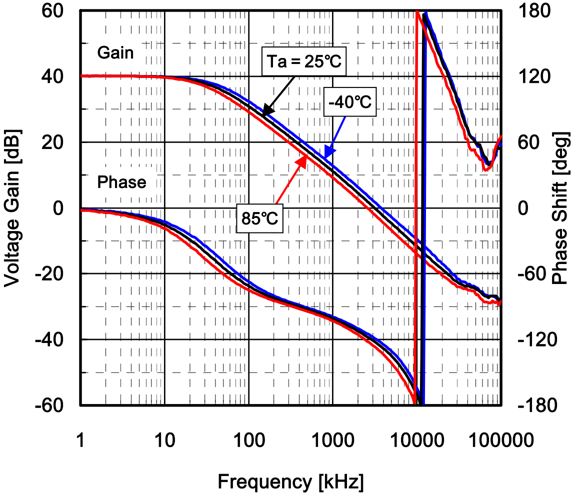
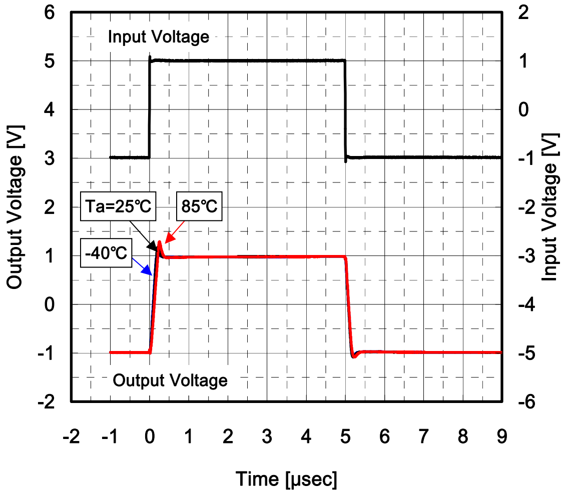


TRANSIENT RESPONSE (TEMPERATURE)

V^+/V^- = ±16V,V_{IN} = 2$V_{P\text{-}P}$,f=100kHz

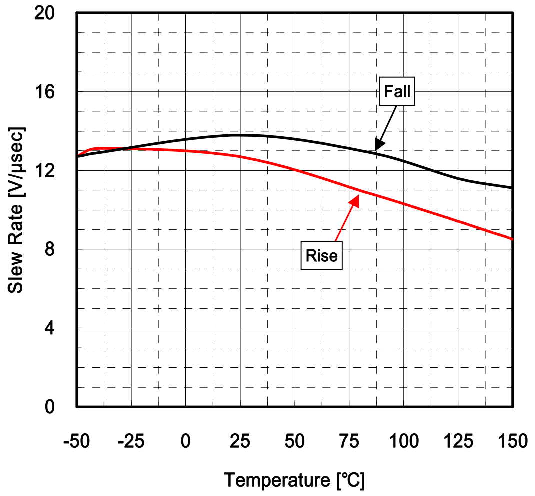
PulseEdge=10nsec,Gv=0dB,C_L=10pF,R_L=2kohm



SLEW RATE vs TEMPERATURE

V^+/V^- = ±16V,V_{IN} = 2$V_{P\text{-}P}$,f=100kHz

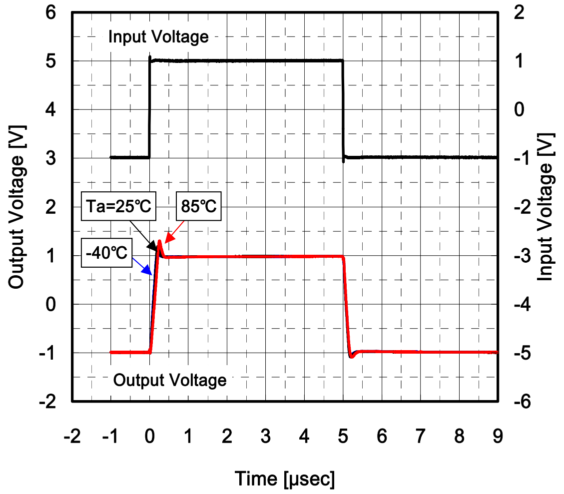
PulseEdge=10nsec,Gv=0dB,C_L=10pF,R_L=2kohm



TRANSIENT RESPONSE (TEMPERATURE)

V^+/V^- = ±15V,V_{IN} = 2$V_{P\text{-}P}$,f=100kHz

PulseEdge=10nsec,Gv=0dB,C_L=10pF,R_L=2kohm



SLEW RATE vs TEMPERATURE

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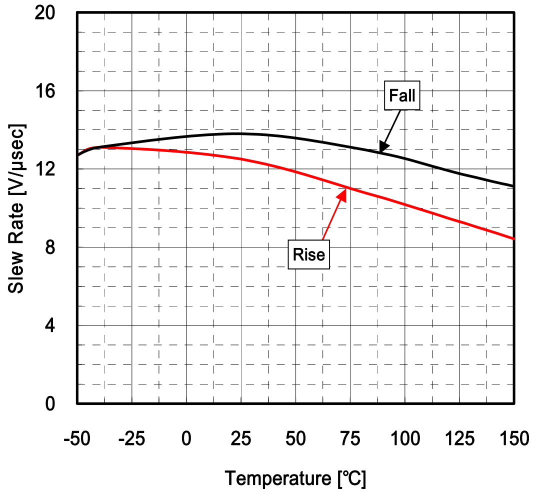
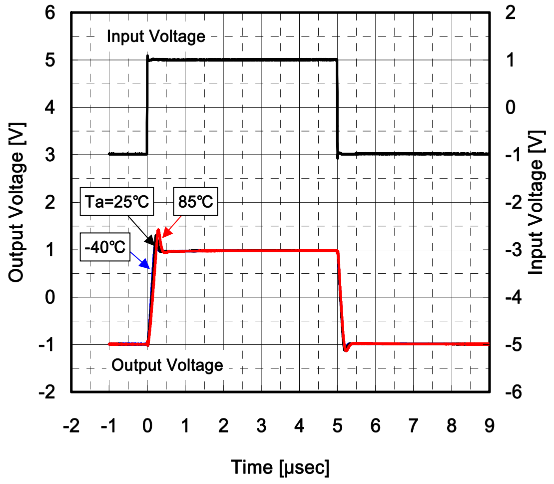
PulseEdge=10nsec,Gv=0dB,C_L=10pF,R_L=2kohm



TRANSIENT RESPONSE (TEMPERATURE)

V^+/V^- = ±9V,V_{IN} = 2$V_{P\text{-}P}$,f=100kHz

PulseEdge=10nsec,Gv=0dB,C_L=10pF,R_L=2kohm



SLEW RATE vs TEMPERATURE

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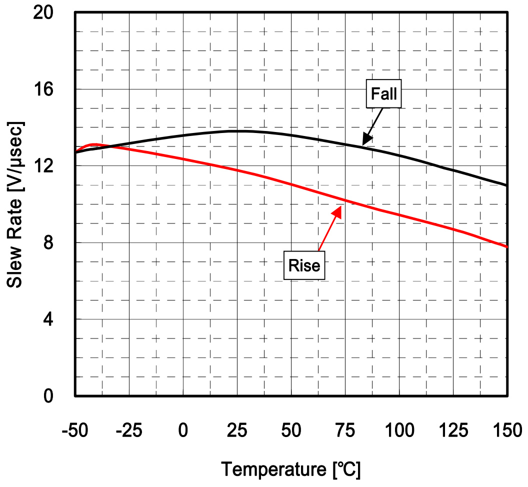
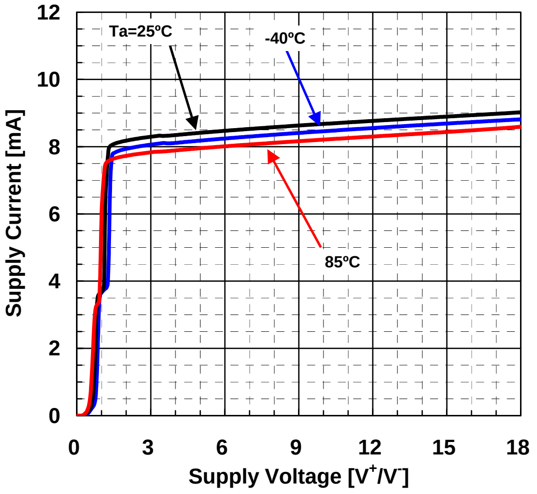
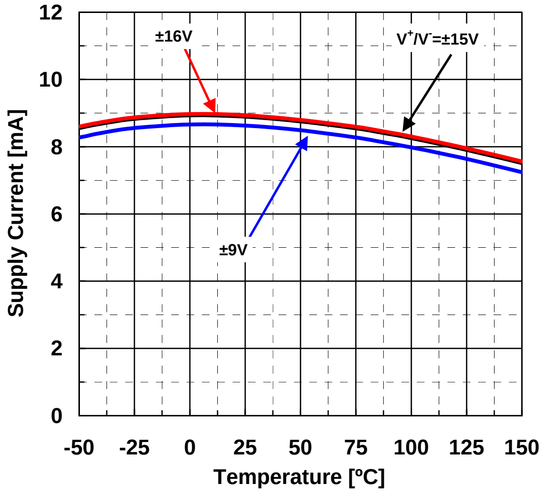


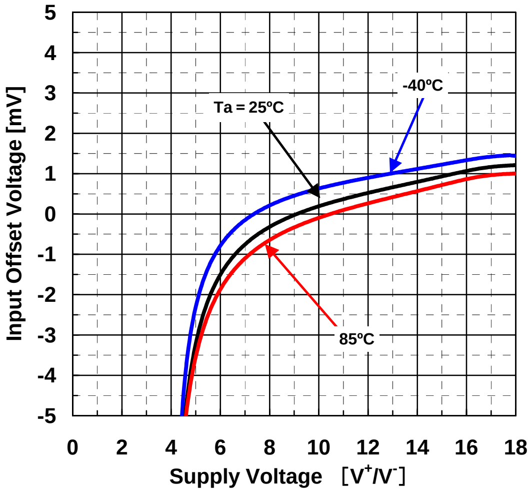
SUPPLY CURRENT vs SUPPLY VOLTAGE
(TEMPERATURE)
G_V=0dB, V_{IN}=0V



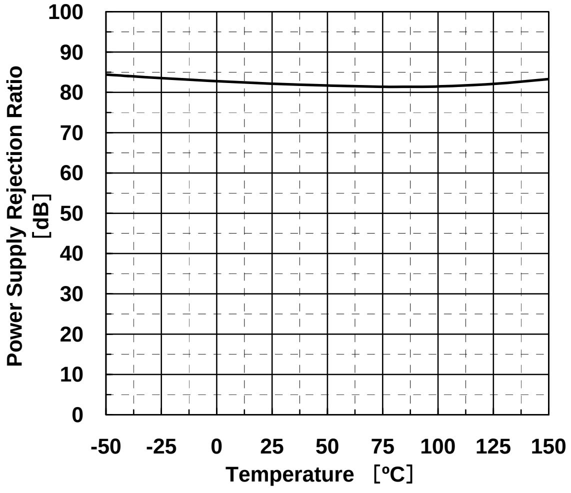
SUPPLY CURRENT vs TEMPERATURE
(SUPPLY VOLTAGE)
G_V=0dB, V_{IN}=0V



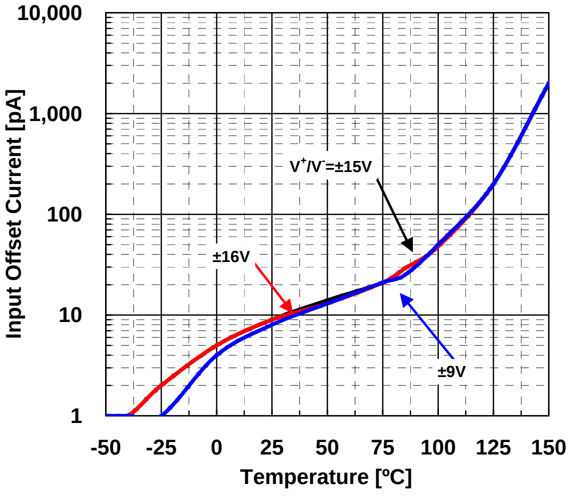
INPUT OFFSET VOLTAGE vs SUPPLY VOLTAGE
(TEMPERATURE)
V_{ICM}=0V, V_{IN}=0V



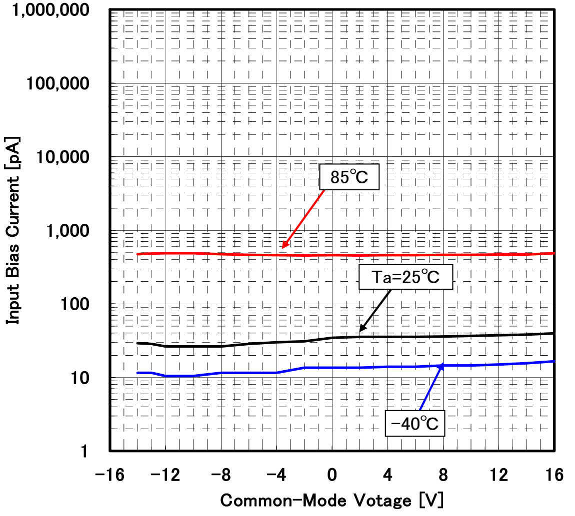
POWER SUPPLY REJECTION RATIO vs TEMPERATURE
V_{ICM}=0V , V^+/V^-=±9V to ±16V



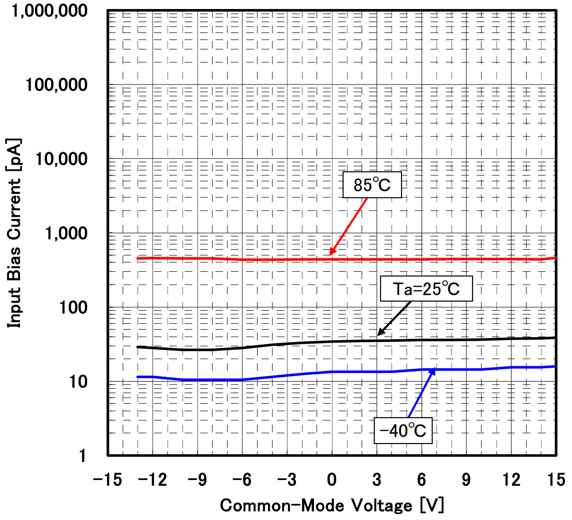
INPUT OFFSET CURRENT vs TEMPERATURE
(SUPPLY VOLTAGE)
V_{ICM}=0V



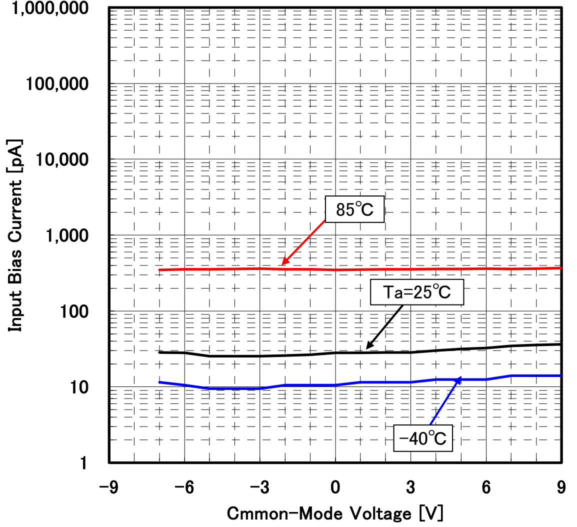
INPUT BIAS CURRENT vs INPUT COMMON-MODE VOLTAGE (TEMPERATURE)
V^+/V^-=±16V



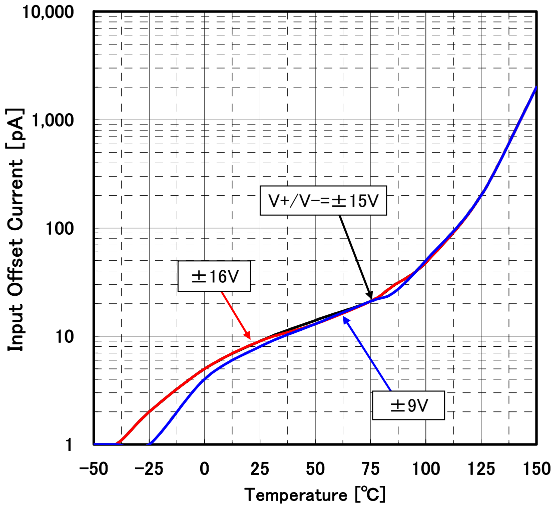
INPUT BIAS CURRENT vs INPUT COMMON-MODE VOLTAGE (TEMPERATURE)
$V^+/V^-=\pm15V$



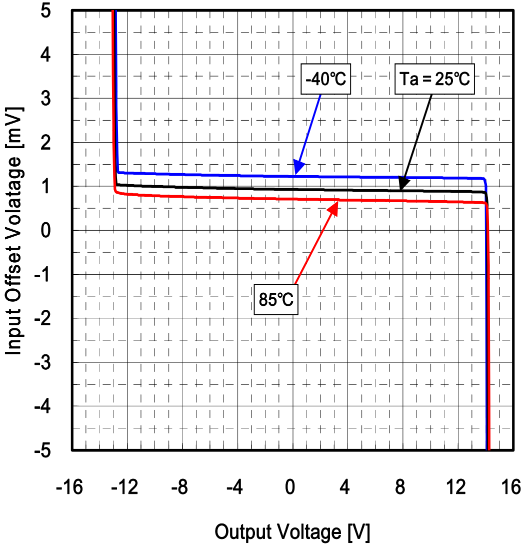
INPUT BIAS CURRENT vs INPUT COMMON-MODE VOLTAGE (TEMPERATURE)
$V^+/V^-=\pm9V$



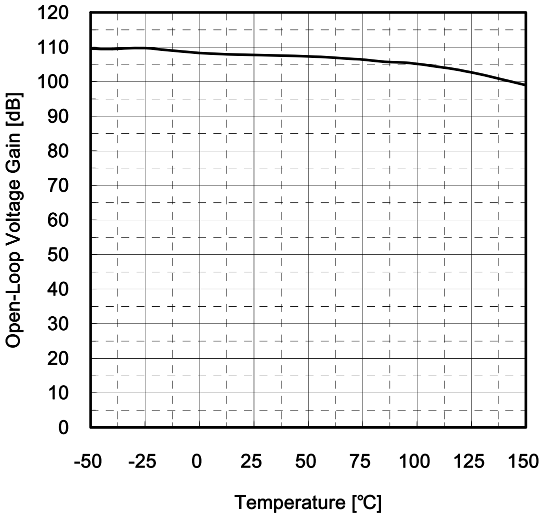
INPUT OFFSET CURRENT vs TEMPERATURE (SUPPLY VOLTAGE)
$V_{ICM}=0V$



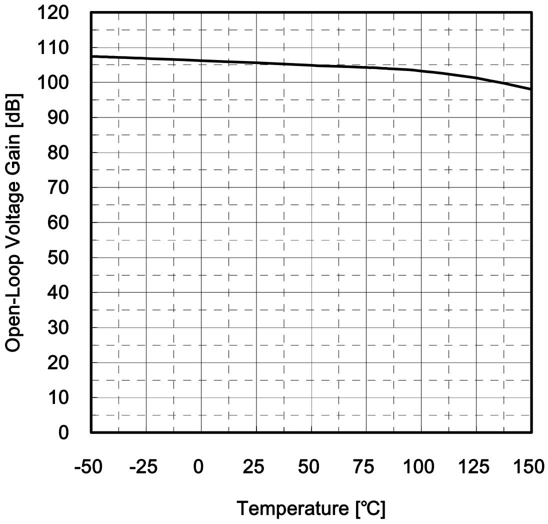
INPUT OFFSET VOLTAGE vs OUTPUT VOLTAGE (TEMPERATURE)
$V^+/V^-=\pm15V$, $R_L=2kohm$ to 0V



OPEN-LOOP VOLTAGE GAIN vs TEMPERATURE
$R_L=2kohm$ to 0V , $V^+/V^-=\pm16V$, Vo=-11V to +11V

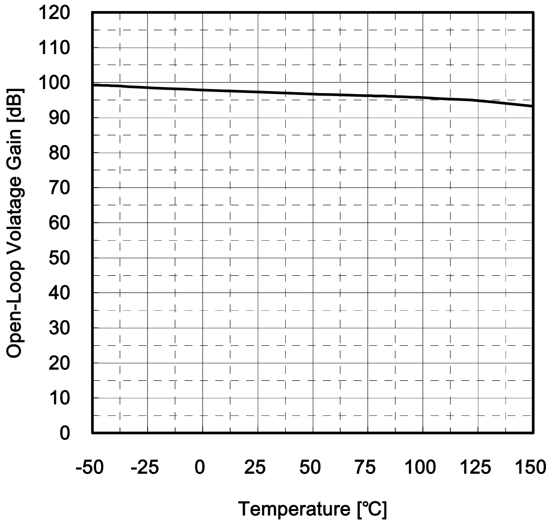


OPEN-LOOP VOLTAGE GAIN vs TEMPERATURE
$R_L=2kohm$ to 0V , $V^+/V^-=\pm15V$, Vo=-10V to +10V



OPEN-LOOP VOLTAGE GAIN vs TEMPERATURE

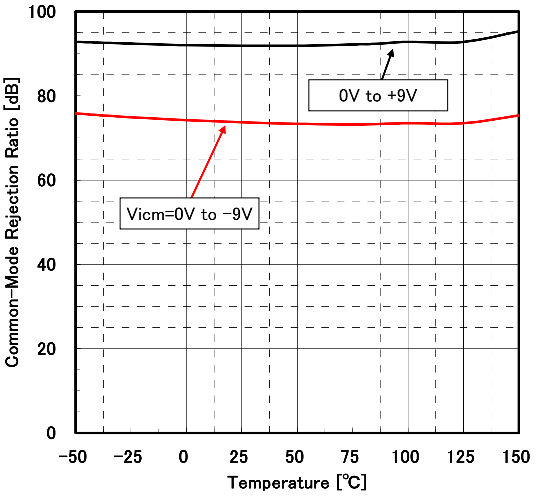
R_L=2kohm to 0V , V^+/V^-=±9V , Vo=-4V to +4V



COMMON-MODE REJECTION RATIO vs TEMPERATUER

(INPUT COMMON-MODE VOLTAGE)

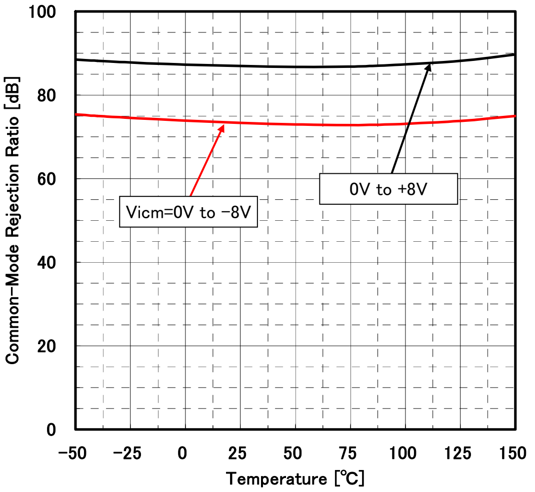
V^+/V^-=±16V



COMMON-MODE REJECTION RATIO vs TEMPERATURE

(INPUT COMMON-MODE VOLTAGE)

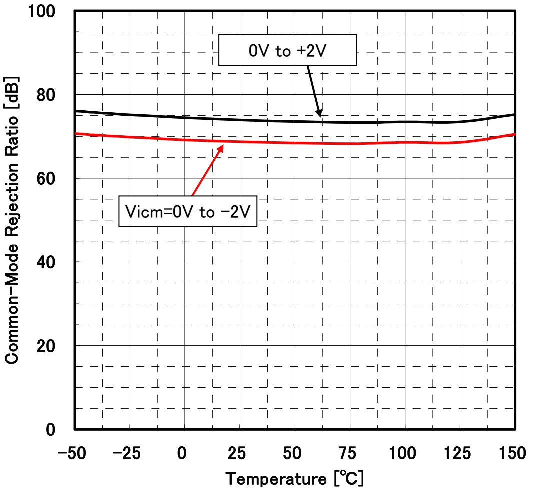
V^+/V^-=±15V



COMMON-MODE REJECTION RATIO vs TEMPERATURE

(INPUT COMMON-MODE VOLTAGE)

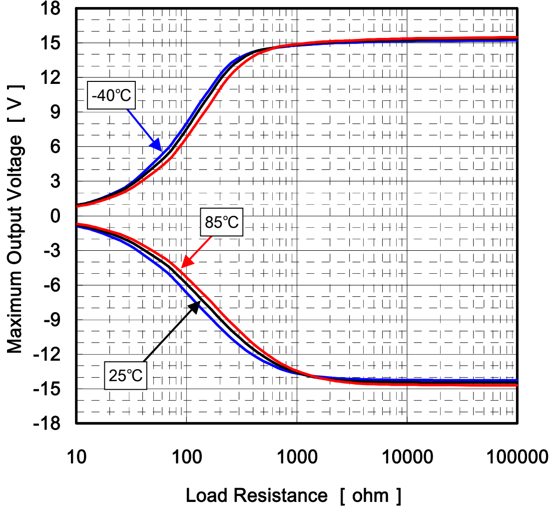
V^+/V^-=±9V



MAXIMUM OUTPUT VOLTAGE vs

LOAD RESISTANCE (TEMPERATURE)

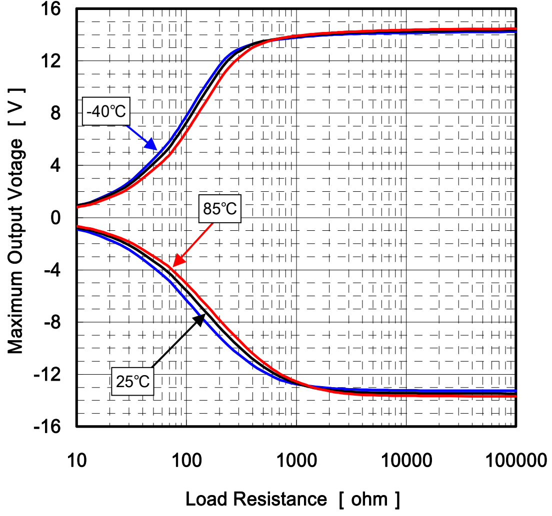
V^+/V^-=±16V,Gv=open,R_L to 0V



MAXIMUM OUTPUT VOLTAGE vs

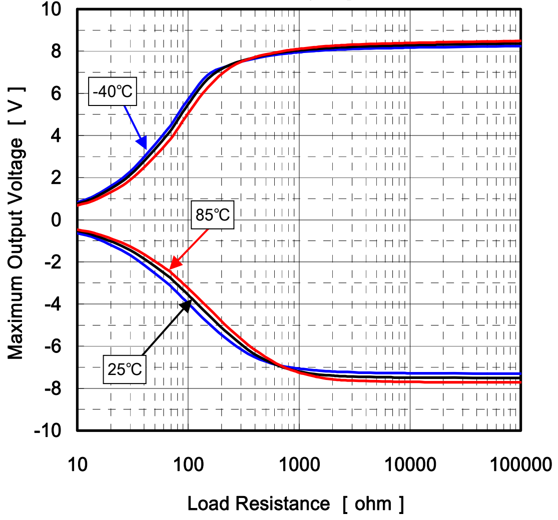
LOAD RESISTANCE (TEMPERATURE)

V^+/V^-=±15V,Gv=open,R_L to 0V



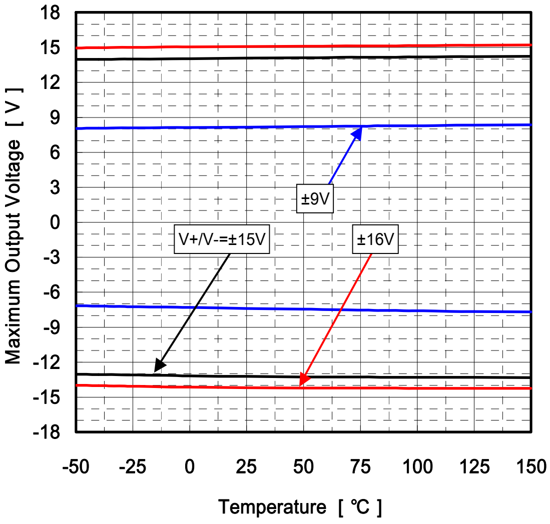
MAXIMUM OUTPUT VOLTAGE vs
LOAD RESISTANCE (TEMPERATURE)

$V^+/V^-=\pm9V$,Gv=open,R_L to 0V



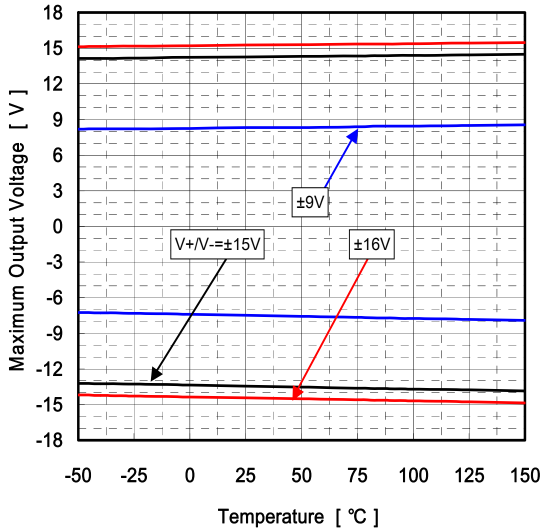
MAXIMUM OUTPUT VOLTAGE vs
TEMPERATURE (SUPPLY VOLTAGE)

Gv=open,R_L=2kohm to 0V



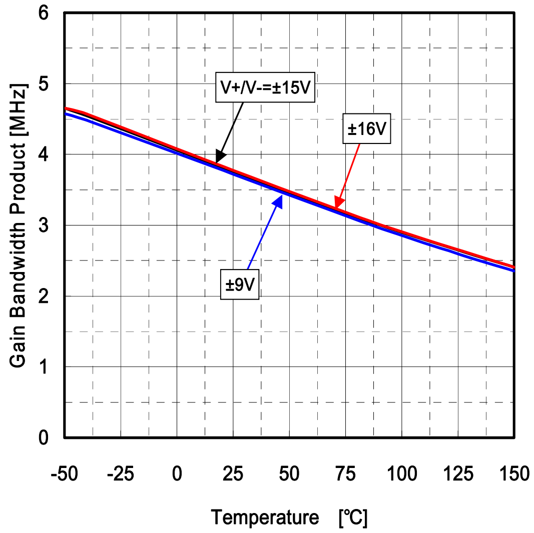
MAXIMUM OUTPUT VOLTAGE vs
TEMPERATURE (SUPPLY VOLTAGE)

Gv=open,R_L=10kohm to 0V



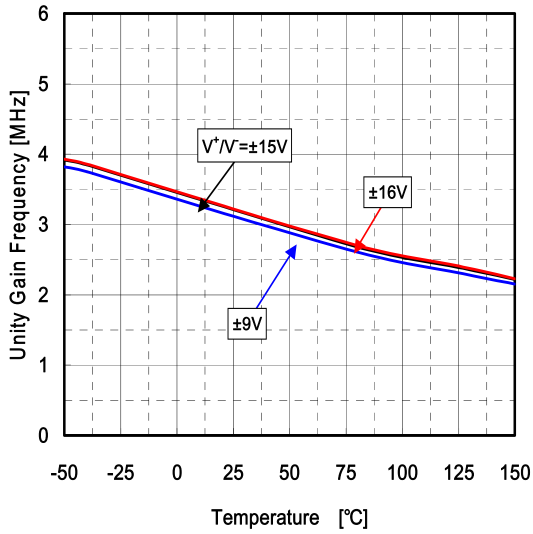
GAIN BANDWIDTH PRODUCT vs TEMPERATURE
(SUPPLY VOLTAGE)

f=10kHz,A_V=80dB, R_S=10ohm, R_T=50ohm,R_L=2kohm, C_L=10pF,V_{IN}=-50dBm



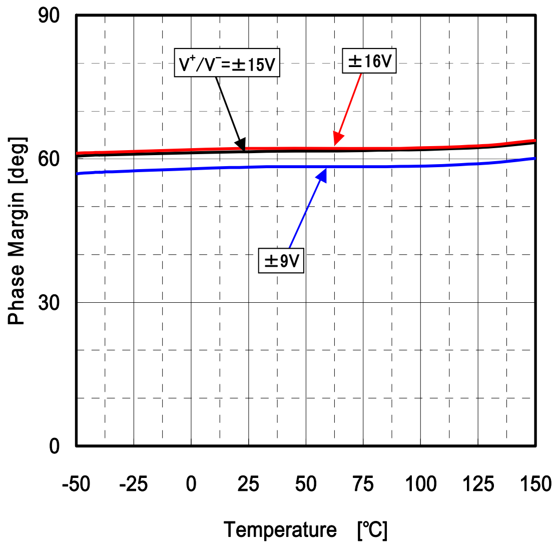
UNITY GAIN FREQUENCY vs TEMPERATURE
(SUPPLY VOLTAGE)

A_V=+100, R_S=100ohm, R_T=50ohm,R_L=2kohm, C_L=56pF,V_{IN}=-30dBm



PHASE MARGIN vs TEMPERATURE
(SUPPLY VOLTAGE)

A_V=+100, R_S=100ohm, R_T=50ohm,R_L=2kohm, C_L=10pF,V_{IN}=-30dBm



MEMO